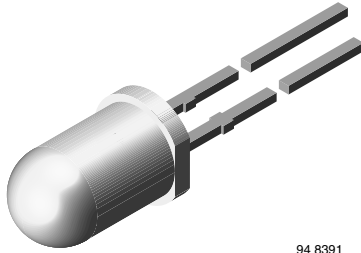


Silicon NPN Phototransistor



94 8391



FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): \varnothing 5
- Leads with stand-off
- High photo sensitivity
- High radiant sensitivity
- Suitable for visible and near infrared radiation
- Fast response times
- Angle of half sensitivity: $\varphi = \pm 20^\circ$
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

Note

** Please see document "Vishay Material Category Policy":
www.vishay.com/doc?99902

APPLICATIONS

- Detector in electronic control and drive circuits

DESCRIPTION

BPW96 is a silicon NPN phototransistor with high radiant sensitivity in clear, T-1 $\frac{3}{4}$ plastic package. It is sensitive to visible and near infrared radiation.

PRODUCT SUMMARY			
COMPONENT	I _{ca} (mA)	φ (deg)	$\lambda_{0.1}$ (nm)
BPW96B	2.5 to 7.5	± 20	450 to 1080
BPW96C	4.5 to 15	± 20	450 to 1080

Note

- Test condition see table "Basic Characteristics"

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
BPW96B	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$
BPW96C	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Collector emitter voltage		V _{CEO}	70	V
Emitter collector voltage		V _{ECO}	5	V
Collector current		I _C	50	mA
Collector peak current	t _p /T ≤ 0.5, t _p ≤ 10 ms	I _{CM}	100	mA
Power dissipation	T _{amb} ≤ 47 °C	P _V	150	mW
Junction temperature		T _j	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C
Storage temperature range		T _{stg}	- 40 to + 100	°C
Soldering temperature	t ≤ 3 s	T _{sd}	260	°C
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R _{thJA}	350	K/W

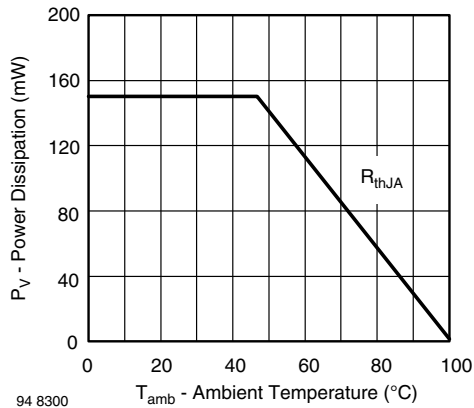


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	$I_C = 1\text{ mA}$	$V_{(BR)CEO}$	70			V
Collector emitter dark current	$V_{CE} = 20\text{ V}, E = 0$	I_{CEO}		1	200	nA
Collector emitter capacitance	$V_{CE} = 5\text{ V}, f = 1\text{ MHz}, E = 0$	C_{CEO}		3		pF
Angle of half sensitivity		φ		± 20		deg
Wavelength of peak sensitivity		λ_p		850		nm
Range of spectral bandwidth		$\lambda_{0.1}$		450 to 1080		nm
Collector emitter saturation voltage	$E_e = 1\text{ mW/cm}^2, \lambda = 950\text{ nm}, I_C = 0.1\text{ mA}$	V_{CEsat}			0.3	V
Turn-on time	$V_S = 5\text{ V}, I_C = 5\text{ mA}, R_L = 100\text{ }\Omega$	t_{on}		2.0		μs
Turn-off time	$V_S = 5\text{ V}, I_C = 5\text{ mA}, R_L = 100\text{ }\Omega$	t_{off}		2.3		μs
Cut-off frequency	$V_S = 5\text{ V}, I_C = 5\text{ mA}, R_L = 100\text{ }\Omega$	f_c		180		kHz

TYPE DEDICATED CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector light current	$E_e = 1\text{ mW/cm}^2, \lambda = 950\text{ nm}, V_{CE} = 5\text{ V}$	BPW96B	I_{ca}	2.5	4.5	7.5	mA
		BPW96C	I_{ca}	4.5	8	15	mA

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

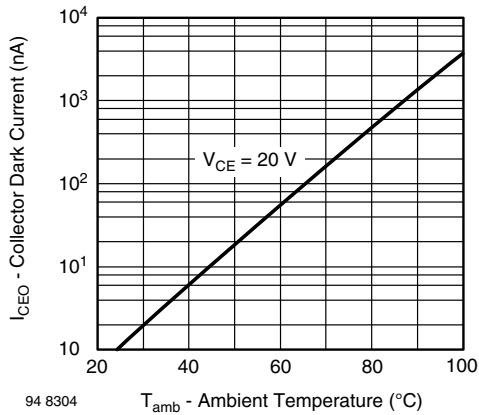


Fig. 1 - Collector Dark Current vs. Ambient Temperature

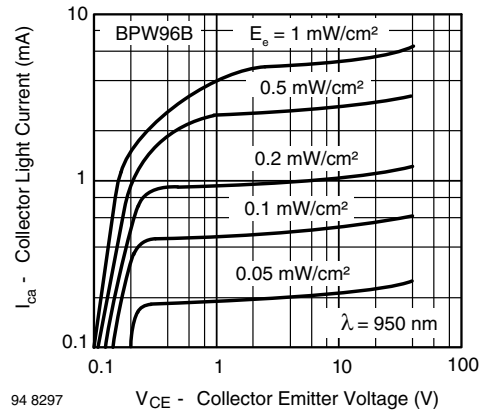


Fig. 4 - Collector Light Current vs. Collector Emitter Voltage

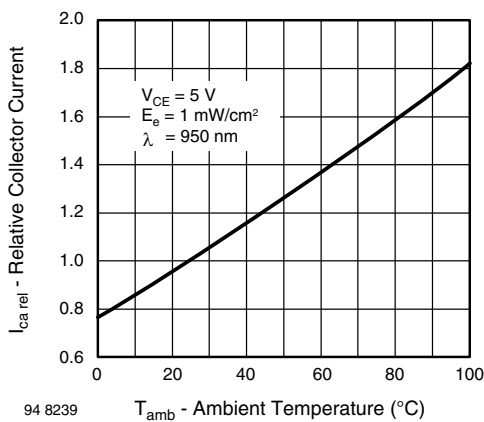


Fig. 2 - Relative Collector Current vs. Ambient Temperature

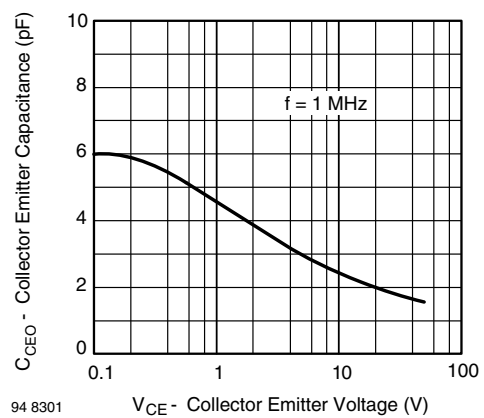


Fig. 5 - Collector Emitter Capacitance vs. Collector Emitter Voltage

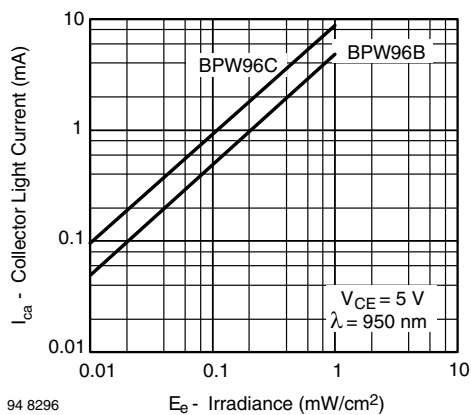


Fig. 3 - Collector Light Current vs. Irradiance

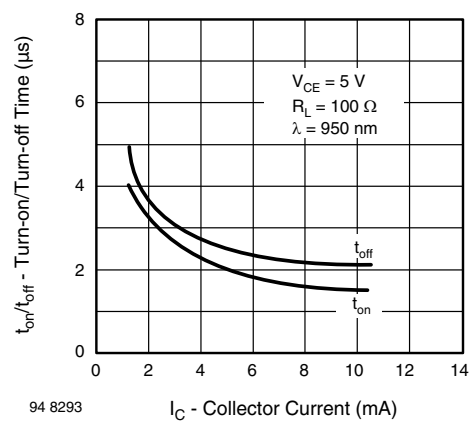


Fig. 6 - Turn-on/Turn-off Time vs. Collector Current

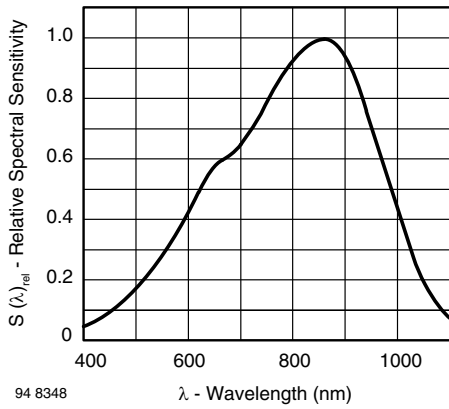


Fig. 7 - Relative Spectral Sensitivity vs. Wavelength

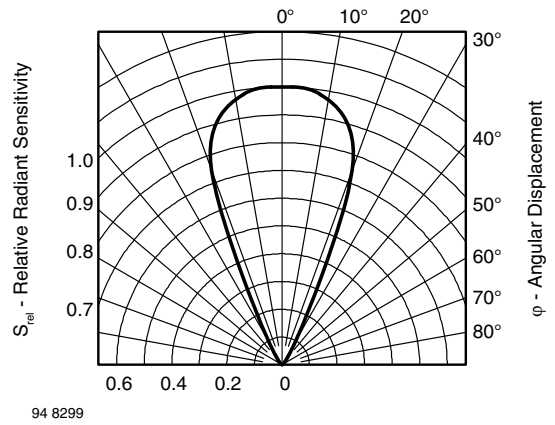
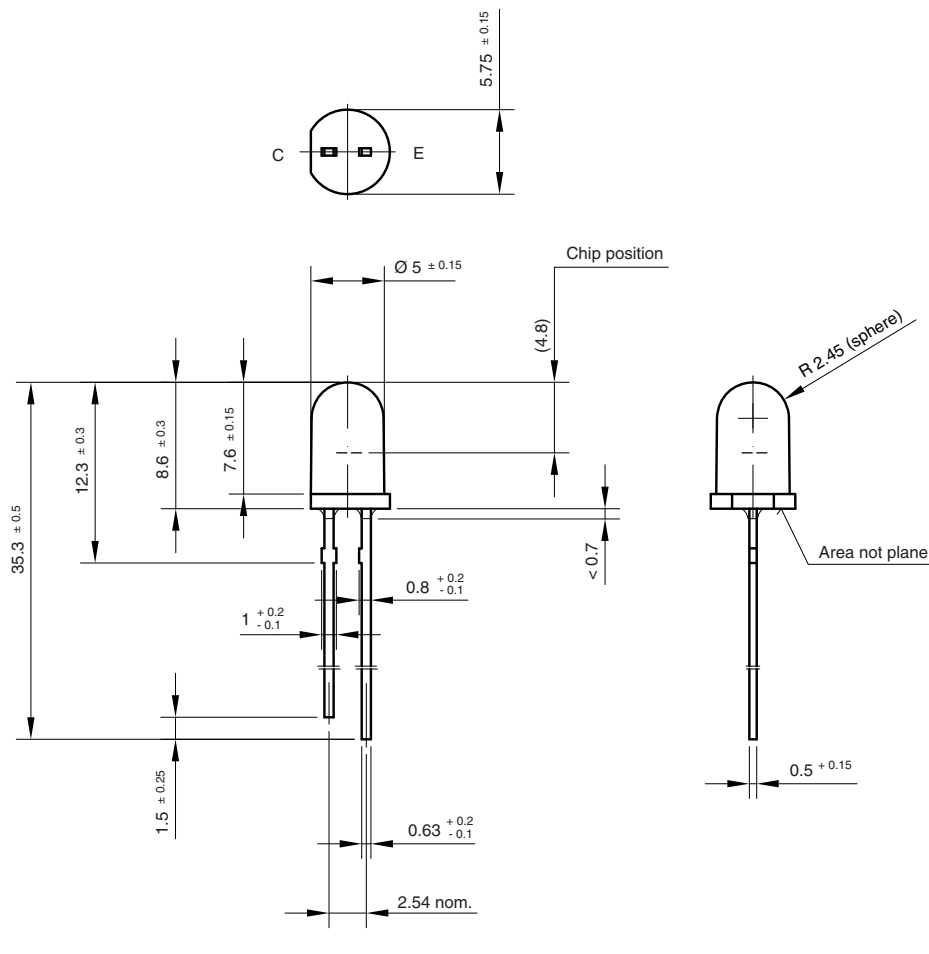


Fig. 8 - Relative Radiant Sensitivity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5086.01-4

Issue:1; 01.07.96

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